

# 74HC1G08-Q100; 74HCT1G08-Q100

## 2-input AND gate

Rev. 2 — 16 August 2012

Product data sheet

### 1. General description

74HC1G08-Q100 and 74HCT1G08-Q100 are high-speed, Si-gate CMOS devices. They provide a 2-input AND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half of those of the 74HC08-Q100 and 74HCT08-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  and from  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\ \Omega$ )
- Multiple package options

### 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC1G08GW-Q100 74HCT1G08GW-Q100	$-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HC1G08GV-Q100 74HCT1G08GV-Q100	$-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads	SOT753



4. Marking

Table 2. Marking codes

Type number	Marking <sup>[1]</sup>
74HC1G08GW-Q100	HE
74HCT1G08GW-Q100	TE
74HC1G08GV-Q100	H08
74HCT1G08GV-Q100	T08

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

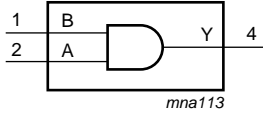


Fig 1. Logic symbol




Fig 2. IEC logic symbol

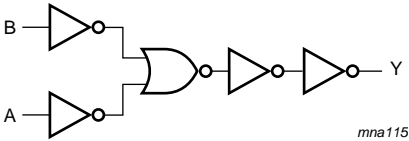


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

74HC1G08-Q100  
74HCT1G08-Q100

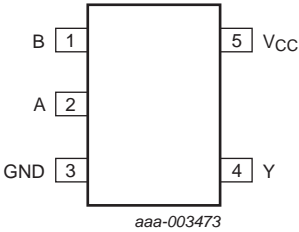


Fig 4. Pin configuration

## 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>CC</sub>	5	supply voltage

## 7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input		Output
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [\[1\]](#)

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	-0.5 V < V <sub>O</sub> < V <sub>CC</sub> + 0.5 V	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	<a href="#">[2]</a> -	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G08-Q100			74HCT1G08-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ °C}$ .

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HC1G08-Q100								
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	V
		I <sub>O</sub> = −2.0 mA; V <sub>CC</sub> = 4.5 V	4.13	4.32	-	3.7	-	V
		I <sub>O</sub> = −2.6 mA; V <sub>CC</sub> = 6.0 V	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 2.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.33	-	0.4	V
		I <sub>O</sub> = 2.6 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	1.0	-	1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10	-	20	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF

**Table 7.** Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HCT1G08-Q100								
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	V
		I <sub>O</sub> = −2.0 mA; V <sub>CC</sub> = 4.5 V	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 2.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	10	-	20	μA
ΔI <sub>CC</sub>	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> − 2.1 V; I <sub>O</sub> = 0 A	-	-	500	-	850	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF

## 11. Dynamic characteristics

**Table 8.** Dynamic characteristics

$GND = 0\text{ V}$ ;  $t_r = t_f \leq 6.0\text{ ns}$ ; All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ . For test circuit see [Figure 6](#)

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit	
			Min	Typ	Max	Min	Max		
74HC1G08-Q100									
t <sub>pd</sub>	propagation delay	A and B to Y; see <a href="#">Figure 5</a>	<a href="#">[1]</a>						
		V <sub>CC</sub> = 2.0 V; C <sub>L</sub> = 50 pF	-	25	115	-	135	ns	
		V <sub>CC</sub> = 4.5 V; C <sub>L</sub> = 50 pF	-	9	23	-	27	ns	
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	7	-	-	-	ns	
		V <sub>CC</sub> = 6.0 V; C <sub>L</sub> = 50 pF	-	8	20	-	23	ns	
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub>	<a href="#">[2]</a>	-	19	-	-	-	pF
74HCT1G08-Q100									
t <sub>pd</sub>	propagation delay	A and B to Y; see <a href="#">Figure 5</a>	<a href="#">[1]</a>						
		V <sub>CC</sub> = 4.5 V; C <sub>L</sub> = 50 pF	-	11	23	-	27	ns	
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	11	-	-	-	ns	

**Table 8. Dynamic characteristics ...continued**  
*GND = 0 V;  $t_r = t_f \leq 6.0$  ns; All typical values are measured at  $T_{amb} = 25$  °C. For test circuit see [Figure 6](#)*

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
$C_{PD}$	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$ <a href="#">[2]</a>	-	21	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  (μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:  
 $f_i$  = input frequency in MHz  
 $f_o$  = output frequency in MHz  
 $C_L$  = output load capacitance in pF  
 $V_{CC}$  = supply voltage in Volts  
 $\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs

12. Waveforms

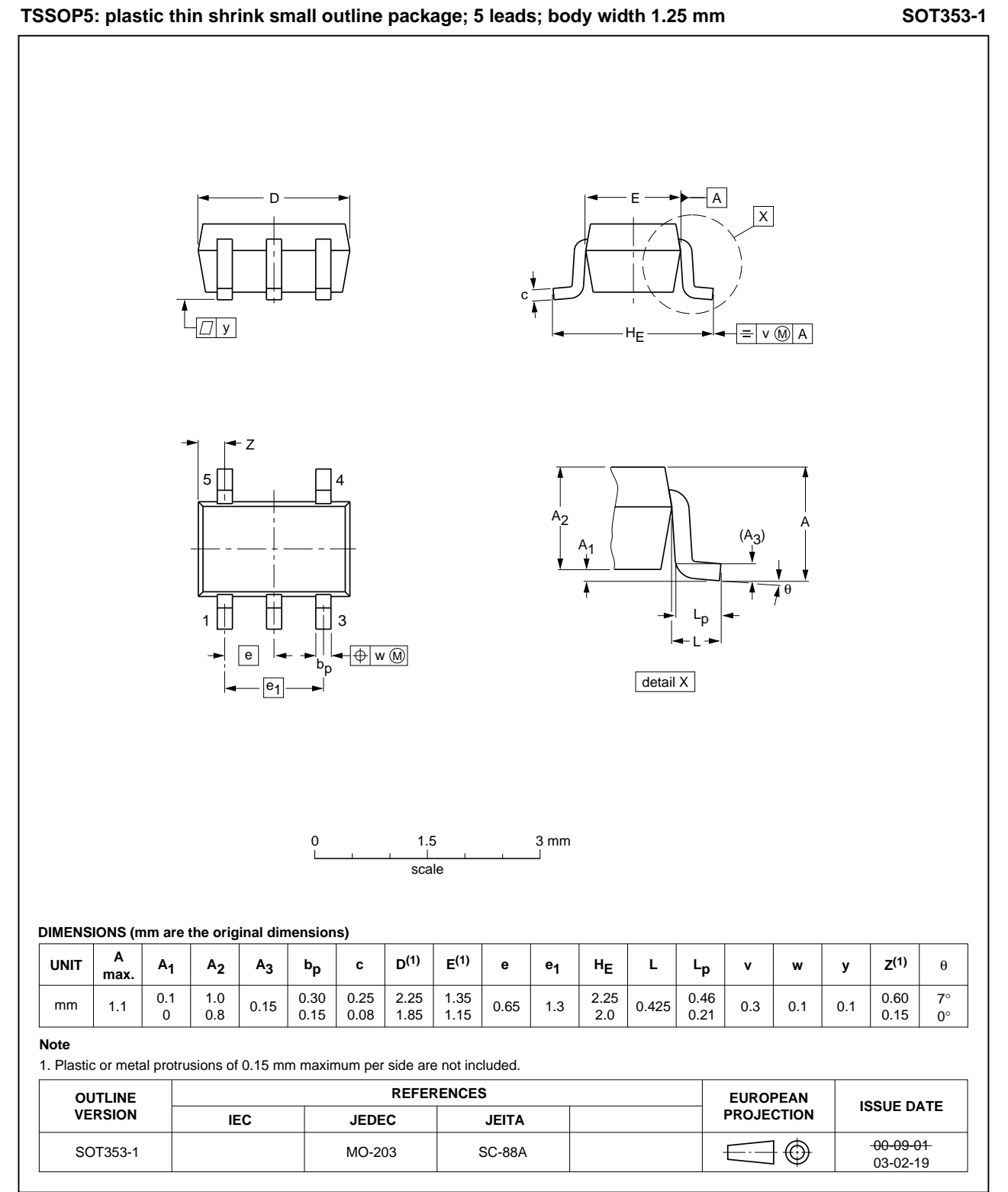
For 74HC1G08-Q100:  $V_M = 0.5 \times V_{CC}$ ;  $V_I = \text{GND to } V_{CC}$   
 For 74HCT1G08-Q100:  $V_M = 1.3 \text{ V}$ ;  $V_I = \text{GND to } 3.0 \text{ V}$

**Fig 5. The input (A and B) to output (Y) propagation delays**

Test data is given in [Table 8](#). Definitions for test circuit:  
 $C_L$  = Load capacitance including jig and probe capacitance  
 $R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator

**Fig 6. Test circuit for measuring switching times**

13. Package outline



Plastic surface-mounted package; 5 leads

SOT753

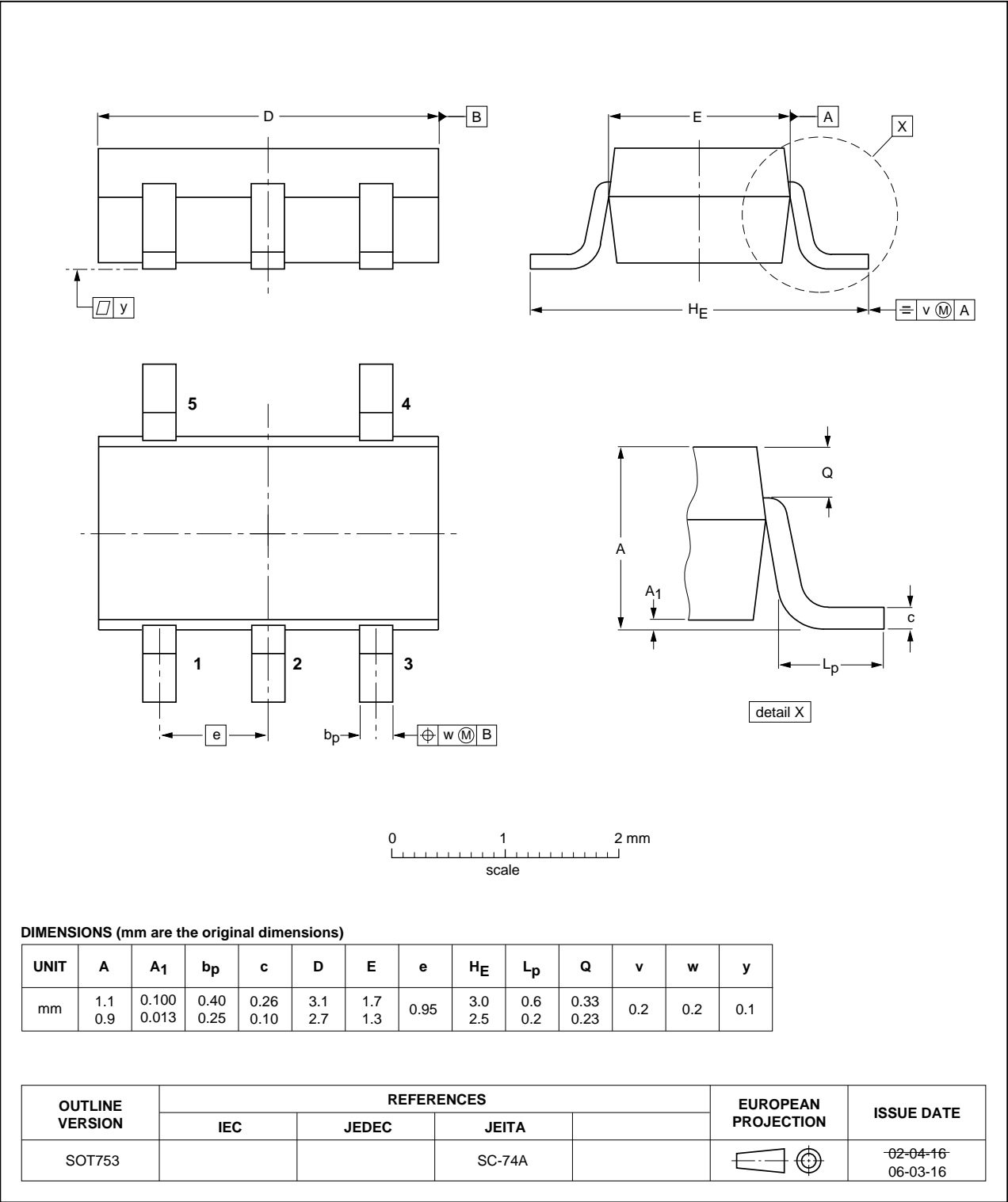


Fig 8. Package outline SOT753 (SC-74A)



## 14. Abbreviations

Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

## 15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G08_Q100 v.2	20120816	Product data sheet	-	74HC_HCT1G08_Q100 v.1
Modifications:	• Added pin 1 location note ( <a href="#">Table 2</a> )			
74HC_HCT1G08_Q100 v.1	20120605	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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